

BF398 is PNP silicon transistor designed for high voltage applications.

TO-92F



CBE

ABSOLUTE MAXIMUM RATINGS

| | | |
|--|----------|---------------|
| Collector-Base Voltage | VCBO | 150V |
| Collector-Emitter Voltage | VCEO | 150V |
| Emitter-Base Voltage | VEBO | 6V |
| Total Power Dissipation | Ptot | 625mW |
| Collector Current | IC | 100mA |
| Operating Junction & Storage Temperature | Tj, Tstg | -55 to +150°C |

ELECTRICAL CHARACTERISTICS (Ta=25°C)

| PARAMETER | SYMBOL | MIN | MAX | UNIT | TEST CONDITIONS |
|--------------------------------------|----------|-----|-----|------|------------------|
| Collector-Base Breakdown Voltage | BVCBO | 150 | | V | IC=10μA IE=0 |
| Collector-Emitter Breakdown Voltage | LVCEO | 150 | | V | IC=10mA IB=0 |
| Emitter-Base Breakdown Voltage | BVEBO | 6 | | V | IE=10μA IC=0 |
| Collector Cutoff Current | ICBO | | 50 | nA | VCB=100V IE=0 |
| Emitter Cutoff Current | IEBO | | 50 | nA | VEB=4V IC=0 |
| D.C. Current Gain | HFE | 25 | | | IC=1mA VCE=10V |
| | | 30 | 200 | | IC=10mA VCE=10V |
| | | 20 | | | IC=100mA VCE=10V |
| Base-Emitter Saturation Voltage | VBE(sat) | 0.6 | 0.9 | V | IC=10mA IB=1mA |
| Collector-Emitter Saturation Voltage | VCE(sat) | | 0.5 | V | IC=10mA IB=1mA |



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